

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A semiconductor device, comprising:  
~~a laminate structure in which an organic insulating film is formed in close contact with a hydrophobic surface of an inorganic insulating film including silicon and nitrogen~~  
a first inorganic insulating film on a semiconductor layer;  
a second inorganic insulating film including silicon and nitrogen on the first inorganic insulating film;  
an organic insulating film formed in close contact with the second inorganic insulating film;  
wherein the first inorganic insulating film and the second insulating film are a nitride; and  
wherein the surface of the second inorganic insulating film has a larger contact angle of water than the surface of the first inorganic insulating film.

2. (Currently Amended) A semiconductor device, comprising:  
[[an]] a first inorganic insulating film having a hydrophobic surface and including silicon and nitrogen on a semiconductor layer; [[and]]  
a second inorganic insulating film including silicon and nitrogen on the first inorganic insulating film;  
an organic insulating film formed in close contact with a hydrophobic surface of the second inorganic insulating film;  
wherein the first inorganic insulating film and the second insulating film are a nitride;  
wherein the surface of the second inorganic insulating film has a larger contact

angle of water than the surface of the first inorganic insulating film; and  
wherein hydrogen concentration in the second inorganic insulating film is higher  
than hydrogen concentration in the first inorganic insulating film.

3. (Currently Amended) A semiconductor device, comprising:  
a first inorganic insulating film on a semiconductor layer;  
a second inorganic insulating film ~~having a hydrophobic surface and~~ including  
silicon and nitrogen on the first inorganic insulating film; ~~[[and]]~~  
an organic insulating film formed in close contact with ~~a hydrophobic surface of~~  
the second inorganic insulating film;  
wherein the first inorganic insulating film and the second insulating film are a  
nitride;  
wherein the surface of the second inorganic insulating film has a larger contact  
angle of water than the surface of the first inorganic insulating film;  
wherein hydrogen concentration in the second inorganic insulating film is higher  
than hydrogen concentration in the first inorganic insulating film; and  
wherein the first inorganic insulating film and the second insulating film are the  
same material.

4. (Canceled)

5. (Currently Amended) A semiconductor device according to Claim 1, wherein  
~~the hydrophobic~~ the second inorganic insulating surface has a contact angle of water of  
equal to or more than 30°.

6. (Currently Amended) A semiconductor device according to Claim 2, wherein  
~~the hydrophobic~~ the second inorganic insulating surface has a contact angle of water of  
equal to or more than 30°.

7. (Currently Amended) A semiconductor device according to Claim 3, wherein ~~the hydrophobic~~ the second inorganic insulating surface has a contact angle of water of equal to or more than 30°.

8. (Currently Amended) A semiconductor device according to Claim 1, wherein ~~the hydrophobic~~ the second inorganic insulating surface has a contact angle of water of equal to or more than 40°.

9. (Currently Amended) A semiconductor device according to Claim 2, wherein ~~the hydrophobic~~ the second inorganic insulating surface has a contact angle of water of equal to or more than 40°.

10. (Currently Amended) A semiconductor device according to Claim 3, wherein ~~the hydrophobic~~ the second inorganic insulating surface has a contact angle of water of equal to or more than 40°.

11. (Original) A semiconductor device according to Claim 1, wherein the inorganic insulating film or the second inorganic insulating film includes oxygen and the nitrogen of equal to or more than 25 atom%.

12. (Original) A semiconductor device according to Claim 2, wherein the inorganic insulating film or the second inorganic insulating film includes oxygen and the nitrogen of equal to or more than 25 atom%.

13. (Original) A semiconductor device according to Claim 3, wherein the inorganic insulating film or the second inorganic insulating film includes oxygen and the nitrogen of equal to or more than 25 atom%.

14. (Original) A semiconductor device according to Claim 1, wherein the inorganic insulating film or the second inorganic insulating film is a silicon nitride film or a silicon nitride oxide film.

15. (Original) A semiconductor device according to Claim 2, wherein the inorganic insulating film or the second inorganic insulating film is a silicon nitride film or a silicon nitride oxide film.

16. (Original) A semiconductor device according to Claim 3, wherein the inorganic insulating film or the second inorganic insulating film is a silicon nitride film or a silicon nitride oxide film.

17. (Currently Amended) A semiconductor device according to Claim 1, wherein the organic insulating film includes one of or a plurality of organic resin materials selected from acrylic resin, polyamide, or polyimide of photosensitive or nonphotosensitive, ~~for example~~.

18. (Currently Amended) A semiconductor device according to Claim 2, wherein the organic insulating film includes one of or a plurality of organic resin materials selected from acrylic resin, polyamide, or polyimide of photosensitive or nonphotosensitive, ~~for example~~.

19. (Currently Amended) A semiconductor device according to Claim 3, wherein the organic insulating film includes one of or a plurality of organic resin materials selected from acrylic resin, polyamide, or polyimide of photosensitive or nonphotosensitive, ~~for example~~.

20.-35. (Canceled)